

/	2016/2		
	23857		00
			()
/	3-3-0		48
		E-Mail	
/	12:00~13:00(2435), 10:00~12:00(2435)		

[] , 1, 2

Schottky pn MOSFET
MOS

Schottky , MOSFET,
1:1, 1:N

가

: 1 1 (1%)
Homework : 15~20 % (가)
/ : 40% , 45 % (가)
가

- [, , MOSFET]
1. MOSFET
- Accumulation, Depletion, Threshold, Inversion
 2. -
 3. 가 :
- []
1. MOSFET -
 2. -
 3. 가 :
- []
- 1.
 - 2.
 3. 가 :

Semiconductor Physics and Devices, Donald Neamen, Fourth Edition, 2012, McGraw-Hill

Ben G. Streetmann, Solid State Electronic Devices, Prentice-Hall
Anderson, Fundamentals of Semiconductor Devices, McGraw-Hill

Chapter Checkpoint, Review Questions, Problems Chapter
1 .

- 1 : Metal-Semiconductor Junction
- 2 : MOS Structure
- 3 : C-V Characteristics of MOS
- 4 : MOSFET Operation
- 5 : Nonideal Effects
- 6 : Scaling
- 7 : Threshold Voltage and Secondary Effects
- 8 :
- 9 : Bipolar Transistor Action and Carrier Distribution
- 10 : Low Frequency Gain
- 11 : Nonideal Effects, Frequency Limitations and Large-Signal Switching
- 12 : Optical Absorption and Solar Cells
- 13 : Photodetection and PL &EL
- 14 : LED and LD
- 15 :

MOSFET
가